

Topological Spin Transport in Quantum Materials and Entanglement

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OUTLINE

- Motivation-Spin Transport Physics in **Quantum Materials & Entanglement....**
- *Theoretical methodologies* to explore spin transport in (disordered) strong SOC topological materials M Vila et al. Phys. Rev. Lett. 124 (19), 196602 (2020) Z. Fan, J.H. Garcia et al Physics Reports 903, 1-69 (2021)
- Multiple components Spin Hall Effect in MoTe, monolayer M. Vila et al. arXiv:2007.02053
- Canted Quantum Spin Hall Effect in WTe, monolayer J.H. Garcia et al. Phys. Rev. Lett. 125, 256603 (2020)



Centre for Advanced 2D Mater





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ROADMAP

JPhys Materials Treat the publicher of the Assential of Physics series Impaction on a reg. / physics series

The 2021 quantum materials roadmap



IOP Publishing









N. Rosen

A. Einstein

PHYSICAL REVIEW

VOLUME 47

Can Quantum-Mechanical Description of Physical Reality Be Considered Complete?

A. EINSTEIN, B. PODOLSKY AND N. ROSEN, Institute for Advanced Study, Princeton, New Jersey (Received March 25, 1935)

In a complete theory there is an element corresponding to each element of reality. A sufficient condition for the reality of a physical quantity is the possibility of predicting it with certainty, without disturbing the system. In quantum mechanics in the case of two physical quantities described by non-commuting operators, the knowledge of one precludes the knowledge of the other. Then either (1) the description of reality given by the wave function in quantum mechanics is not complete or (2) these two quantities cannot have simultaneous reality. Consideration of the problem of making predictions concerning a system on the basis of measurements made on another system that had previously interacted with it leads to the result that if (1) is false then (2) is also false. One is thus led to conclude that the description of reality as given by a wave function is not complete.



of them with a representative of its own. I would not call that one but rather the characteristic trait of quantum mechanics, the one that enforces its entire departure from classical lines of thought. By the interaction the two representatives (or ψ -functions) have become entangled. To disentangle them we must gather further information by experiment, although we knew as much as any-

"Problem solved by violation Of the Bell's inequality..."

Einstein Podosly Rosen « thought experiment» Quantum Entanglement

(practical?) Quantum Computers

- IBM Q System One : 56-qubit machine
- INTEL; D-Wave 2000Q quantum annealer
- Microsoft Quantum Lab-Delft
- Google Quantum Artificial Intelligence Lab
- Bristlecone: 72-qubit quantum chip

aims to build quantum processors and develop novel quantum algorithms to dramatically accelerate computational tasks for machine learning

Spintronics and its industrial/Societal impact

Magnetic field sensors used to read data in hard disk drives, microelectromechanical systems (MEMS), minimally invasive surgery Automotive sensors for fuel handling system, Anti-skid system, speed control & navigation Magnetoresistive random-access memory (MRAM) Spin transfer Torque MRAM

Spin-based information processing ?

Need for spin information transport on long distance (room T) Spin injection and detection (ferromagnets/non magnetic materials)

Active devices based on **Spin manipulation** ?

Datta-Das spin transistor

Spin Hall Effect

Spin torques (SOT-MRAM) Spin current

Spin Hall effect

(Pure) **spin current** generation, manipulation & detection

Spin- orbit coupling fields (effective magnetic field) **Generates (bulk) transversal spin current** (spin polarization orthogonal to both currents)

$$\vec{J_s} = \theta_{sH}\vec{\sigma} \wedge \vec{J_c}$$

Spin Hall angle :

measures how much spin current is generated from a charge current

(strong spin-orbit coupling materials)

Long sought-after spintronic materials

 λ_s

Spin diffusion length : measures upper limit for spin transmission

J. Sinova, S. O. Valenzuela et al. **Rev. Mod. Phys. 87**, 1213 (2015)

SHE in Low-symmetry multilayers TMDs

Nano Letters 19 (12), 8758-8766 (2019) C. K. Safeer, et al.

Multidirectional spin-to-charge conversion in multilayers $MoTe_2$ (11 nm thick sample)

Pure spin current injected in graphene channel & adsorbed in MoTe₂ – converted into charge current (nonlocal voltage)

 $\lambda_{\rm s}.\theta_{sH} \sim 1 \text{ nm}$

P. Song et al. *Nat. Mater.* **19**, 292–298 (2020)

MoTe, multilayers

 $\theta_{sH} \sim 30\%$ $\lambda_{\rm s} \sim 1 \mu m$

 $\lambda_{\rm s}.\theta_{sH} \sim 300 {\rm nm} !!$

 $\Delta R_{sH} \sim \theta_{sH}^2 \rho \frac{W}{\lambda_s} e^{-L/\lambda_s}$

Quantum Spin Hall Effect

E/t

0

C.L. Kane and E. J. Mele, **Phys. Rev. Lett. 95**, **26801 (2005)**

Zigzag graphene ribbon with intrinsic SOC

$$\mathcal{H} = t \sum_{\langle ij \rangle} c_i^{\dagger} c_j + i(8\lambda_{SO}/a^2) \sum_{\langle \langle ij \rangle \rangle} c_i^{\dagger} \mathbf{s}.(\mathbf{d}_{ij}^1 \times \mathbf{d}_{ij}^2) c_j$$

Gapless helical edge states States with opposite spins counterpropagate at the edges

"QHE" in absence of magnetic field Towards dissipation current (TRS invariant)....

 $2\pi/a$

π/a

k_x

 $\Delta_g \sim 0.1 \mathrm{meV}$

First experimental evidence of 2D topological insulators

1T'-TMD monolayer as QSH insulators

Prediction in 2014

X. Qian, J. Liu, L. Fu, J. Li, Science 346, 1344 (2014)

Structural distortion causes an intrinsic band inversion between chalcogenide-p and metal-d bands (*gap in order of 0.1 eV*)

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Topological field effect transistor *(low-power quantum electronics)*

1T-WTe, as Quantum Spin Hall insulator

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TOPOLOGICAL MATTER

Observation of the quantum spin Hall effect up to 100 kelvin in a monolayer crystal

Wu et al. Science 359, 76-79 (2018)

Purely electrical measurements

Spin-momentum locking (entanglement) has not yet been directly visualized/demonstrated

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 J.H. Garcia et al. Phys. Rev. Lett. 125, 256603 (2020)

Order N quantum transport methods (Kubo, (Spin)-Hall Kubo, Landauer-Büttiker)

Linear Scaling Quantum Transport Methodologies

Zheyong Fan,^{1, 2} Jose Hugo Garcia,³ Aron W. Cummings,³ Jose-Eduardo Barrios,³ Michel Panhans,⁴ Ari Harju,⁵ Frank Ortmann,⁴ and Stephan Roche^{3, 6}

Disorder systems, Magnetic fields, **Charge transport Thermal transport** (phonon dynamics-harmonic approx.) **Electron-phonon coupling** (molecular dynamics, Tdependence) **Polaron transport**, **Spin transport** (SOC)

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Spin dynamics of propagating wavepacket

$$\left\langle \Psi_{\perp}(0) \right\rangle = \begin{pmatrix} 1 \\ 0 \end{pmatrix} |\varphi_{RP}\rangle \quad |\Psi(t)\rangle = e^{-i\hat{\mathcal{H}}t/\hbar} |\Psi(0)\rangle$$

$$s_i(t) = |\Psi_i^{\uparrow}(t)|^2 - |\Psi_i^{\downarrow}(t)|^2$$

(time-dependent) Local spin density in real space

$$\frac{\Psi(t)|\sigma_z\delta(E-\hat{\mathcal{H}})+\delta(E-\hat{\mathcal{H}})\sigma_z|\Psi(t)\rangle}{2\langle\Psi(t)|\delta(E-\hat{\mathcal{H}})|\Psi(t)\rangle}$$

Spin Hall Kubo conductivity

(SHE in dissipative regime)

$$\sigma_{\rm sH} = \frac{e\hbar}{\Omega} \sum_{m,n} \frac{f(E_m) - f(E_n)}{E_m - E_n} \frac{\mathcal{I}m[\langle m | J_x^z | n \rangle \langle n | v_y | m \rangle]}{E_m - E_n + i\eta},$$

$$J_x^z = \frac{\hbar}{4} \{ \sigma_z, v_x \} \text{ is the spin current operator} \qquad \qquad \theta_{sH} = \frac{\sigma_{xy}^z}{\sigma_{xx}}$$
$$\sigma_{sH} = \frac{e\hbar}{\Omega} \int du dv \frac{f(u) - f(v)}{(u - v)^2 + \eta^2} j(u, v),$$

$$j(u,v) = \sum_{m,n} \mathcal{I}m[\langle m | J_x^z | n \rangle \langle n | v_y | m \rangle] \delta(u - E_m) \delta(v - E_n)$$

= $\sum_{m,n}^M (4\mu_{mn}g_m g_n T_m(\hat{u})T_n(\hat{v}))/((1 + \delta_{m,0})(1 + \delta_{n,0})\pi^2 \sqrt{(1 - \hat{u}^2)(1 - \hat{v}^2)}),$
 $\mu_{mn} = \frac{4}{\Delta E^2} \mathcal{I}m[Tr[J_x^z T_n(\hat{H})v_y T_m(\hat{H})]]$

The trace in μ_{mn} is computed by the average on a small number $R \ll N$ of random phase vectors $|\varphi\rangle$

$$\sigma_{xx} = \frac{2\hbar e^2}{\pi\Omega} \sum_{m,n=0}^{M} \mathcal{I}m[g_m(\epsilon + i\eta)]\mathcal{I}m[g_n(\epsilon + i\eta)]\mu_{mn}$$

dc-Kubo conductivity

Nonlocal resistance simulation

EXCELENCIA SEVERO OCHOA charge current injectec from lead 2 to 1 while I_0 (multiterminal geometry) a non-local voltage $R_{\rm NL} = (V_3 - V_4)/I_0$ $I_p = \sum_q G_{pq}(V_p - V_q)$ kwant **Charge current** $G_{pq} = \frac{e^2}{h} \int dE \operatorname{Tr}[\mathbf{t}_{pq}\mathbf{t}_{pq}^{\dagger}](-\partial f/\partial E)$ \mathbf{t}_{pq} the transmission matrix between transverse propagating Spin current modes within semi-infinite leads p and q $I_n^{s_\alpha} \quad G_{pq}^{s_\alpha} = \frac{e^2}{h} \int dE \operatorname{Tr}[s_\alpha \mathbf{t}_{pq} \mathbf{t}_{pq}^{\dagger}] (-\partial f / \partial E)$ $\theta_{sH} = \frac{I^{s_z}}{I_0}$

Study of spin dynamics (crossover)

Brute force simulation of the non-local resistance versus channel length

Hanle spin precession simulations

M. Vila, J.H. Garcia, A.W. Cummings, S. Power, C. Groth, X. Waintal, S. Roche Physical Review Letters 124 (19), 196602 (2020)

Spin Hall Effect and Origins of Nonlocal Resistance in Adatom-Decorated Graphene

D. Van Tuan,^{1,2} J. M. Marmolejo-Tejada,^{3,4} X. Waintal,⁵ B. K. Nikolić,^{3,*} S. O. Valenzuela,^{1,6} and S. Roche^{1,6,†} ¹Catalan Institute of Nanoscience and Nanotechnology (ICN2), CSIC and The Barcelona Institute of Science and Technology, Campus UAB, Bellaterra, 08193 Barcelona, Spain ²Department of Electrical and Computer Engineering, University of Rochester, Rochester, New York 14627, USA ³Department of Physics and Astronomy, University of Delaware, Newark, Delaware 19716-2570, USA ⁴School of Electrical and Electronics Engineering, Universidad del Valle, Cali AA 25360, Colombia ⁵Univ. Grenoble Alpes, INAC-PHELIQS, F-38000 Grenoble, France and CEA, INAC-PHELIQS, F-38000 Grenoble, France ⁶ICREA—Institució Catalana de Recerca i Estudis Avançats, 08010 Barcelona, Spain (Received 19 February 2016; published 20 October 2016)

Kubo formalism (dissipative & Hall conductivities)

Multiterminal landauer-Büttiker formalism

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 M. Vila et al. arXiv:2007.02053
- Canted Quantum Spin Hall Effect in WTe₂ monolayer
 J.H. Garcia et al. arXiv:2007.05626

Scalable production of stable 1T'-MoTe₂

380 Jun 380 Jun 300 µm

www.acsnano.org

Synthesis of Large-Scale Monolayer 1T'-MoTe₂ and Its Stabilization *via* Scalable hBN Encapsulation

Simona Pace,* Leonardo Martini, Domenica Convertino, Dong Hoon Keum, Stiven Forti, Sergio Pezzini, Filippo Fabbri, Vaidotas Mišeikis, and Camilla Coletti*

CVD growth of monolayer 1T'-MoTe₂with a lateral size up to 500 µm & its scalable encapsulation via semidry transfer of few-layer CVD hBN

Optical image of as-grown monolayer 1T'-MoTe₂ single crystals on a SiO₂ growth substrate

4-band symmetry-based model TMD-1T_d

4-band symmetry-based model TMD-1T_d

Anisotropic spin dynamics in MoTe₂

Study of the nonlocal resistance versus channel length to extract spin diffusion length

arXiv:2007.02053

of a 1D spin diffusion equation

Anisotropic spin dynamics in MoTe,

In 2D Rashba SOC materials **Spin-momentum locking**

scattering changes effective (in-plane) *magnetic field randomly*

In 2D Weyl semimetal TMD Persistent (canted) spin texture

$$\theta \equiv \arctan\left(\Lambda_z/\Lambda_y\right) \approx -56^\circ$$

Effective magnetic field is fixed (pointing in the yz plane) x-polarized spins precess much faster- shorter spin diffusion z-polarized spins precess faster than y-polarized

 $\lambda_{\mathrm{s}}^{y} > \lambda_{\mathrm{s}}^{z} \gg \lambda_{\mathrm{s}}^{x}$

Spin accumulation & (Giant) Spin Hall angle

Experimental fingerprints (Hanle)

Simulated response of the inverse SHE (R_{ISHE}) to spin precession for two orientations of the TMD crystal (full absorption limit)

spin current polarization reaching the TMD J_s^{α} controlled externally with a magnetic field orientation

Anisotropic spin diffusion

$$R_{ISHE} = V_{ISHE} / I_0^y$$

- up to 3 orders of magnitude larger than other SHE materials (large SHA)
- symmetric or antisymmetric depending on crystal orientation

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QSHE: MoTe₂ vs WTe₂

Spin Hall conductivity for WTe₂

Simulations on a system with **4 Millions atoms** (energy broadening = 5meV)

In the gap

$$|\sigma_{xy}^{\alpha}| \equiv \sqrt{(\sigma_{xy}^y)^2 + (\sigma_{xy}^z)^2} = \frac{2e^2}{h}$$

two spin-canted topological states sustaining QSHE in WTe₂

$$\arctan \left(\sigma_{xy}^{z} / \sigma_{xy}^{y} \right) = -56^{\circ}$$

(spin quantization axis)

Spin Hall conductivity tensor (Kubo-Bastin formula) $\sigma^{lpha}_{ij}, lpha=x,y,z\;$ measures of the spin projection onto lpha $\sigma_{ij}^{\alpha} = -2\hbar\Omega \int_{-\infty}^{E_{\rm F}} dE \operatorname{Im} \left(\operatorname{Tr} \left[\delta(E - \mathcal{H}) J_{s,i}^{\alpha} \frac{dG^{+}}{dE} J_{j} \right] \right)$ σ_{xy}^{α} 1 $\sigma^{\alpha}_{xy} \left(e^2 / h \right)$ $^{-1}$ -1.0-0.50.00.5 $E - E_{\rm F} \,({\rm eV})$ $U(\theta) \equiv \cos\left[\left(2\theta - \pi\right)/4\right]\sigma_0 - i\sin\left[\left(2\theta - \pi\right)/4\right]\sigma_x$ $\mathcal{H}'_{\rm SOC} \equiv U^{\dagger}(\theta) \mathcal{H} U(\theta) = \Lambda_x k_y \sigma_x + \Lambda_r k_x \sigma_{z'} \tau_x$ $[\mathcal{H}', \sigma_{z'}] \approx 0$ (spin preserved along z')

Nonlocal resistance calculations

TopologicallyQuantized two-terminal resistance (2 channels) $h/2e^2$ protected edge-statesQuantized nonlocal resistance $2h/3e^2$

Robustness to disorder (Anderson model 1 eV)

Bond-projected spin currents for spins polarized along the (rotated) **z**' **direction**

Bond-projected spin currents for spins polarized along the (rotated) y' direction

 $oldsymbol{J}_{ extsf{s}}^{y^{*}}$

"vanishing contribution"

M. Vila et al. arXiv:2007.02053

Determination of the helical edge and bulk spin axis in quantum spin Hall insulator WTe2

Wenjin Zhao¹[†], Elliott Runburg¹[†], Zaiyao Fei¹, Joshua Mutch¹, Paul Malinowski¹, Bosong Sun¹, Xiong Huang^{2,3}, Dmytro Pesin⁴, Yong-Tao Cui^{2,3}, Xiaodong Xu^{1,5}, Jiun-Haw Chu¹, David H. Cobden¹*

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²Department of Physics and Astronomy, University of California, Riverside, Riverside CA 92521, USA

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†These authors contributed equally

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Entanglement in Quantum Materials

Particles in Graphene

Three intraparticle (quantum) degrees Spin Valley "isospín" Sublattice "pseudospin"

8-components wavefunction

(0	$p_x - ip_y$	0	0	0	0	0	0	\rangle	$\begin{pmatrix} \Psi_{A,+} \\ \Psi^{\uparrow} \end{pmatrix}$
$p_x - i p_y$	0	0	0	0	0	0	0		$\Psi_{B,+}^{"}$
0	0	0	$-p_x + ip_y$	0	0	0			$\Psi^{\scriptscriptstyle \Pi}_{A,-}$
0	0	$-p_x + ip_y$	0	0	0	0	0		$\Psi^{\Uparrow}_{B,-}$
0	0	0	0	0	$p_x - ip_y$	0	0		Ψ_{A+}^{\Downarrow}
0	0	0	0	$p_x - i p_y$	0	0	0		$\Psi_{D}^{\downarrow\downarrow}$
0	0	0	0	0	0	0	$-p_x + ip_y$		${}^{-B,+}_{\Psi}$
0	0	0	0	0	0	$-p_x + ip_y$	0		$\overset{\Psi}{}_{A,-}$
									$\langle \Psi_{B,-}^{\prime} \rangle$

No intervalley/spin mixing- Valleys degenerate.. No disorder, No spin-orbit interaction

$$\mathcal{H}_{K_+} = v_F \vec{\sigma}.\vec{p}$$

DIRAC Fermions GAPLESS Linear energy dispersion and velocity 10⁶m/s

/γτ(

Long range potential Intravalley scattering (short momentum transfer)

Anomalous quantum transport

- Ballistic conductivity $\sigma \sim 4e^2/\pi h$
- Klein tunneling
- Diverging zero-energy Mean free path/mobility
- Weak antilocalization (quantum interferences)
- Anomalous vs conventional QHE
- Spin transport ?

Pseudospin-driven spin relaxation mechanism in graphene

Dinh Van Tuan^{1,2}, Frank Ortmann^{1,3,4}, David Soriano¹, Sergio O. Valenzuela^{1,5} and Stephan Roche^{1,5}*

$$\vec{P}(E,t) = \frac{\langle \psi_{\uparrow}(t) | [1_{\sigma} \otimes \vec{s}] \,\delta(E - \mathcal{H}^{\text{eff}}) + \delta(E - \mathcal{H}^{\text{eff}}) [1_{\sigma} \otimes \vec{s}] |\psi_{\uparrow}(t)\rangle}{2\langle \psi_{\uparrow}(t) | \delta(E - \mathcal{H}^{\text{eff}}) |\psi_{\uparrow}(t)\rangle}$$

Emergence of intraparticle entanglement and time-varying violation of Bell's inequality in Dirac matter

Bruna Gabrielly de Moraes^(D),^{1,2} Aron W. Cummings^(D),¹ and Stephan Roche^{1,3,*}

¹Catalan Institute of Nanoscience and Nanotechnology (ICN2), CSIC and BIST, Campus UAB, Bellaterra, 08193 Barcelona, Spain ²Department of Physics, Universitat Autónoma de Barcelona, Campus UAB, Bellaterra, 08193 Barcelona, Spain ³Institució Catalana de Recerca i Estudis Avançats (ICREA), 08010 Barcelona, Spain

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We demonstrate the emergence and dynamics of intraparticle entanglement in massless Dirac fermions. This entanglement, generated by spin-orbit coupling, arises between the spin and sublattice pseudospin of electrons in graphene. The entanglement is a complex dynamic quantity but is generally large, independent of the initial state. Its time dependence implies a dynamical violation of a Bell inequality, while its magnitude indicates that large intraparticle entanglement is a general feature of graphene on a substrate. These features are also expected to impact entanglement between pairs of particles, and may be detectable in experiments that combine Cooper pair splitting with nonlocal measurements of spin-spin correlation in mesoscopic devices based on Dirac materials.

Emerging entanglement properties between intraparticle degrees of freedom **Robustness** against decoherence Possibility of nonlocal manipulation...

Concurrence (*entanglement degree*) $R = \sqrt{\rho_{1,2}(\sigma_{1y} \otimes \sigma_{2y})\rho_{1,2}^*(\sigma_{1y} \otimes \sigma_{2y})}$

diagonalising an operator R which is built from the general two-qubit density matrix

$$C(\phi) = max\{0, \tilde{\lambda_1} - \tilde{\lambda_2} - \tilde{\lambda_3} - \tilde{\lambda_4}\}$$

Concurrence has a one-to-one correlation with the entanglement of formation, and ranges between **0** (separable state) and **1** (maximally entangled state)

Concurrence (spin-pseudospin) for electronic states propagating in Graphene/substrate (SiO₂ or hBN)

$$\hat{\mathcal{H}} = \hbar v_{\mathrm{F}} \left(\tau \hat{\sigma}_x k_x + \hat{\sigma}_y k_y \right) \otimes \hat{s}_0 + \lambda_{\mathrm{R}} \left(\tau \hat{\sigma}_x \otimes \hat{s}_y - \hat{\sigma}_y \otimes \hat{s}_x \right)$$

Spin and pseudospin will precess around **effective magnetic and pseudomagnetic fields** (oscillation freq. $\omega_{\rm R} = 2\lambda_{\rm R}/\hbar$)

$$\begin{aligned} \boldsymbol{B}_{\boldsymbol{s}}^{\text{eff}}(t) &= \lambda_{\text{R}} \left(-\langle \hat{\sigma}_{y} \rangle(t) , \langle \hat{\sigma}_{x} \rangle(t) , 0 \right), \\ \boldsymbol{B}_{\boldsymbol{\sigma}}^{\text{eff}}(t) &= \lambda_{\text{R}} \left(\langle \hat{s}_{y} \rangle(t) , -\langle \hat{s}_{x} \rangle(t) , 0 \right) \\ &+ \varepsilon \left(1 , 0 , 0 \right), \end{aligned}$$

Emergence and Resilience of Spin-Pseudospin entanglement

is a separable state with random spherical angles defining the orientations of the pseudospin and spin on the Bloch sphere

$$|\psi_n^r\rangle = \begin{bmatrix} a & b & c & d \end{bmatrix}^{\mathrm{T}}$$

States that are equivalent to the action of a random unitary matrix on some reference state, which are uniform over the four-dimensional Hilbert space

Even arbitrarily initial state develops a final entanglement (entanglement resilient to scattering)

Time-dependent violation of the Bell inequality (CHSH variant) *for intraparticle degrees of freedom*

Generalization to nonlocal correlations between interparticle DoF

Manipulation **by gauge fields** (electromagnetic, deformation fields, proximity effects...)

 $e^{-i\hat{\mathcal{H}}t/\hbar} |\Psi_{1,k_0};\Psi_{2,-k_0}\rangle \otimes \left(|\Uparrow_1^z \Downarrow_2^z\rangle - |\Downarrow_1^z \Uparrow_2^z\rangle\right)$

Barrier(s